Features :

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{RSM}	V_{RRM}	品名
900V	800V	Mx110D80
1100V	1000V	Mx110D100
1300V	1200V	Mx110D120
1500V	1400V	Mx110D140
1700V	1600V	Mx110D160
1900V	1800V	Mx110D180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(℃)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100℃	150			110	A
$I_{F(RMS)}$	RMS forward current		150			173	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			10	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			2.60	kA
I^2t	I^2t for fusing coordination					33	A^2s*10^3
V_{FO}	Threshold voltage		150			0.80	V
r_F	Forward slope resistance					1.74	mΩ
V_{FM}	Peak forward voltage	I_{FM}=330A	25			1.45	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine, Single side cooled per chip				0.35	℃/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	At 180°sine, Single side cooled per chip				0.20	℃/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min, I_{iso}:1mA(max)		3000			V
F_m	Terminal connection torque(M5)			2.4		3.0	N·m
	Mounting torque(M6)				6		N·m
T_{vj}	Junction temperature			-40		150	℃
T_{stg}	Stored temperature			-40		125	℃
W_t	Weight				170		g
Outline	M01						

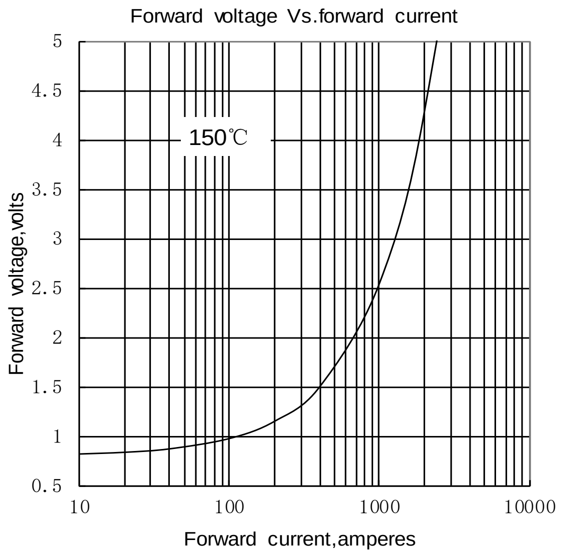


Fig.1

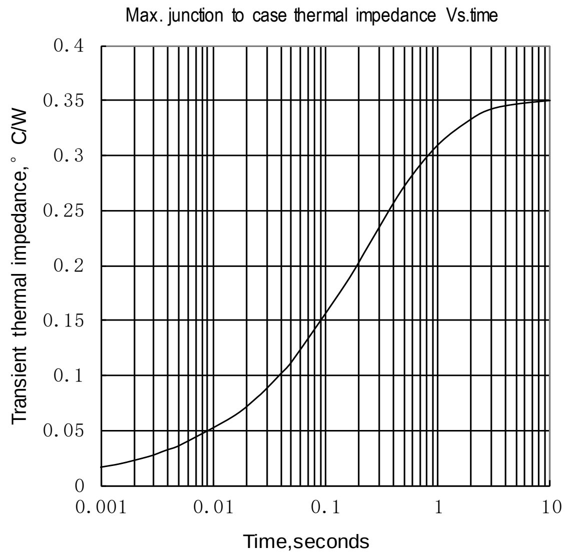


Fig.2

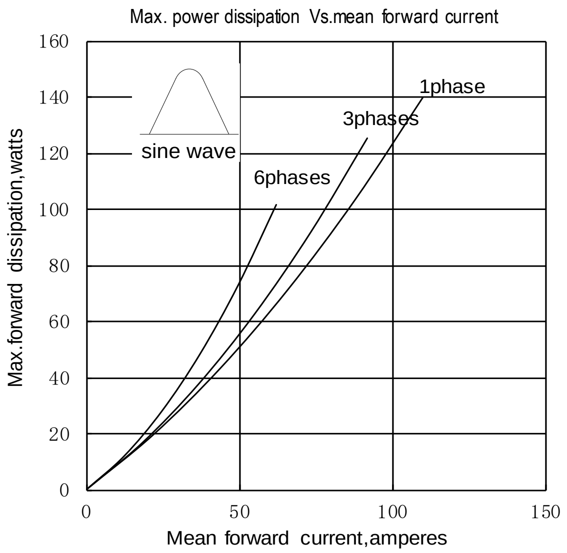


Fig.3

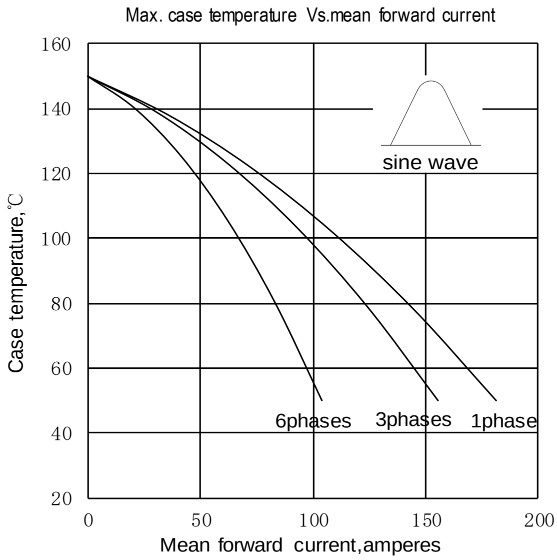


Fig.4

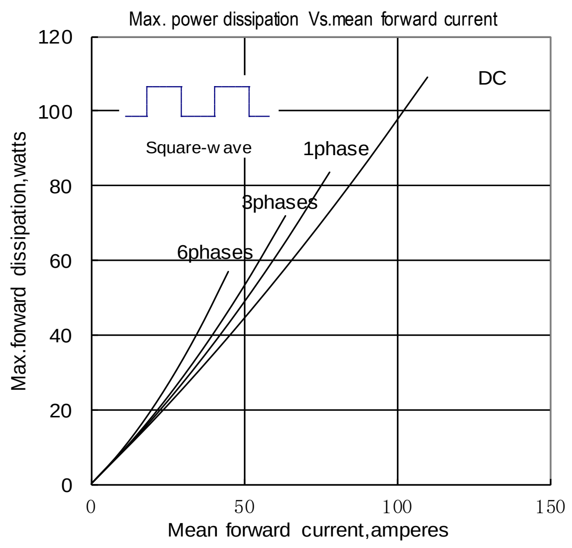


Fig.5

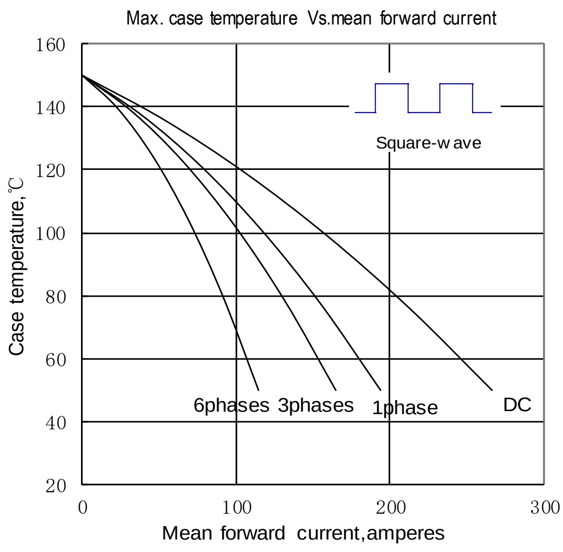


Fig.6

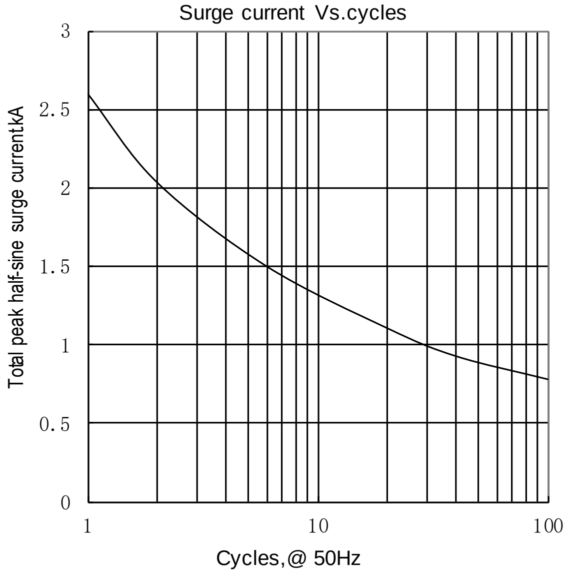


Fig.7

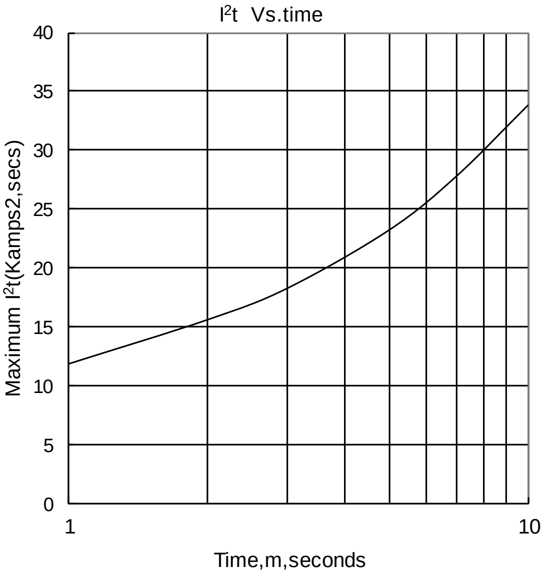
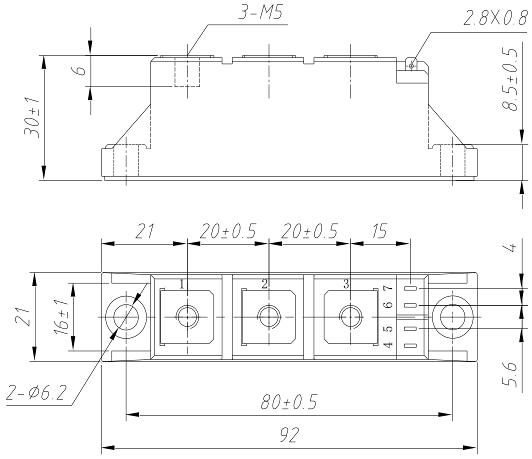
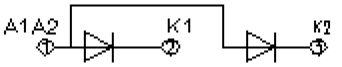


Fig.8



MR110D**



MC110D**